

## SILICON POWER TRANSISTOR

# 2SA1008

### PNP SILICON EPITAXIAL TRANSISTOR FOR HIGH-SPEED SWITCHING

The 2SA1008 is a mold power transistor developed for high-speed switching, and is ideal for use as a driver in devices such as switching regulators, DC/DC converters, and high-frequency power amplifiers.

#### ORDERING INFORMATION

| Part No. | Package  |
|----------|----------|
| 2SA1008  | TO-220AB |

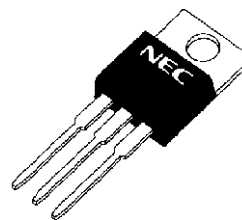
#### FEATURES

- Low collector saturation voltage
- Fast switching speed
- Complementary transistor: 2SC2331

#### ABSOLUTE MAXIMUM RATINGS ( $T_A = 25^\circ\text{C}$ )

| Parameter                    | Symbol         | Conditions                                      | Ratings     | Unit             |
|------------------------------|----------------|-------------------------------------------------|-------------|------------------|
| Collector to base voltage    | $V_{CBO}$      |                                                 | -100        | V                |
| Collector to emitter voltage | $V_{CEO}$      |                                                 | -100        | V                |
| Emitter to base voltage      | $V_{EBO}$      |                                                 | -7.0        | V                |
| Collector current (DC)       | $I_{C(DC)}$    |                                                 | -2.0        | A                |
| Collector current (pulse)    | $I_{C(pulse)}$ | $PW \leq 300 \mu s$ ,<br>duty cycle $\leq 10\%$ | -4.0        | A                |
| Base current (DC)            | $I_{B(DC)}$    |                                                 | -1.0        | A                |
| Total power dissipation      | $P_T$          | $T_C = 25^\circ\text{C}$                        | 15          | W                |
|                              |                | $T_A = 25^\circ\text{C}$                        | 1.5         | W                |
| Junction temperature         | $T_j$          |                                                 | 150         | $^\circ\text{C}$ |
| Storage temperature          | $T_{stg}$      |                                                 | -55 to +150 | $^\circ\text{C}$ |

(TO-220AB)



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# ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = 25°C)

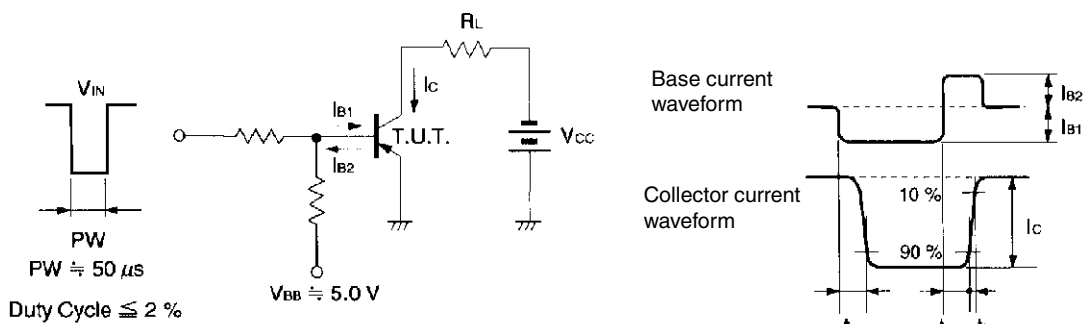
| Parameter                    | Symbol                 | Conditions                                                                                                                                         | MIN. | TYP. | MAX. | Unit |
|------------------------------|------------------------|----------------------------------------------------------------------------------------------------------------------------------------------------|------|------|------|------|
| Collector to emitter voltage | V <sub>CE0(SUS)</sub>  | I <sub>C</sub> = -1.0 A, I <sub>B1</sub> = -0.1 A, L = 1 mH                                                                                        | -100 |      |      | V    |
| Collector to emitter voltage | V <sub>CEX(SUS)1</sub> | I <sub>C</sub> = -1.0 A, I <sub>B1</sub> = -I <sub>B2</sub> = -0.1 A, V <sub>BE(OFF)</sub> = 5.0 V, L = 180 μH, clamped                            | -100 |      |      | V    |
| Collector to emitter voltage | V <sub>CEX(SUS)2</sub> | I <sub>C</sub> = -2.0 A, I <sub>B1</sub> = -0.2 A, I <sub>B2</sub> = 0.1 A, V <sub>BE(OFF)</sub> = 5.0 V, L = 180 μH, clamped                      | -100 |      |      | V    |
| Collector cutoff current     | I <sub>CBO</sub>       | V <sub>CB</sub> = -100 V, I <sub>E</sub> = 0 A                                                                                                     |      |      | -10  | μA   |
| Collector cutoff current     | I <sub>CER</sub>       | V <sub>CE</sub> = -100 V, R <sub>BE</sub> = 51 Ω, T <sub>A</sub> = 125°C                                                                           |      |      | -1.0 | mA   |
| Collector cutoff current     | I <sub>CEx1</sub>      | V <sub>CE</sub> = -100 V, V <sub>BE(OFF)</sub> = 1.5 V                                                                                             |      |      | -10  | μA   |
| Collector cutoff current     | I <sub>CEx2</sub>      | V <sub>CE</sub> = -100 V, V <sub>BE(OFF)</sub> = 1.5 V, T <sub>A</sub> = 125°C                                                                     |      |      | -1.0 | mA   |
| Emitter cutoff current       | I <sub>EBO</sub>       | V <sub>EB</sub> = -5.0 V, I <sub>C</sub> = 0 A                                                                                                     |      |      | -10  | μA   |
| DC current gain              | h <sub>FE1</sub>       | V <sub>CE</sub> = -5.0 V, I <sub>C</sub> = -0.1 A <sup>Note</sup>                                                                                  | 40   |      |      |      |
| DC current gain              | h <sub>FE2</sub>       | V <sub>CE</sub> = -5.0 V, I <sub>C</sub> = -1.0 A <sup>Note</sup>                                                                                  | 40   |      | 200  |      |
| Collector saturation voltage | V <sub>CE(sat)</sub>   | I <sub>C</sub> = -1.0 A, I <sub>B</sub> = -0.1 A <sup>Note</sup>                                                                                   |      |      | -0.6 | V    |
| Base saturation voltage      | V <sub>BE(sat)</sub>   | I <sub>C</sub> = -1.0 A, I <sub>B</sub> = -0.1 A <sup>Note</sup>                                                                                   |      |      | -1.5 | V    |
| Turn-on time                 | t <sub>on</sub>        | I <sub>C</sub> = -1.0 A, R <sub>L</sub> = 50 Ω, I <sub>B1</sub> = -I <sub>B2</sub> = -0.1 A, V <sub>CC</sub> ≅ -50 V<br>Refer to the test circuit. |      |      | 0.5  | μs   |
| Storage time                 | t <sub>stg</sub>       |                                                                                                                                                    |      |      | 1.5  | μs   |
| Fall time                    | t <sub>f</sub>         |                                                                                                                                                    |      |      | 0.5  | μs   |

**Note** Pulse test PW ≤ 350 μs, duty cycle ≤ 2%

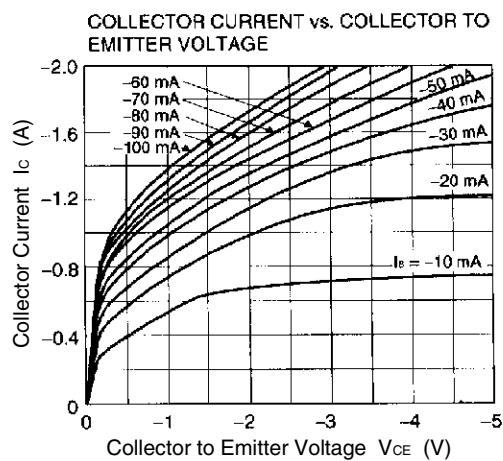
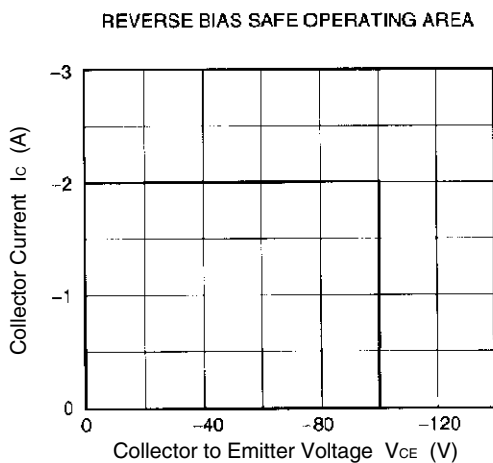
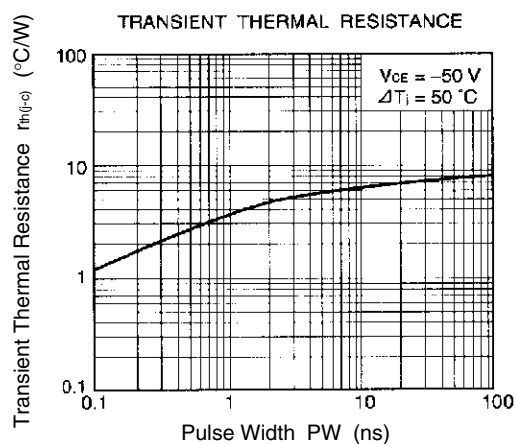
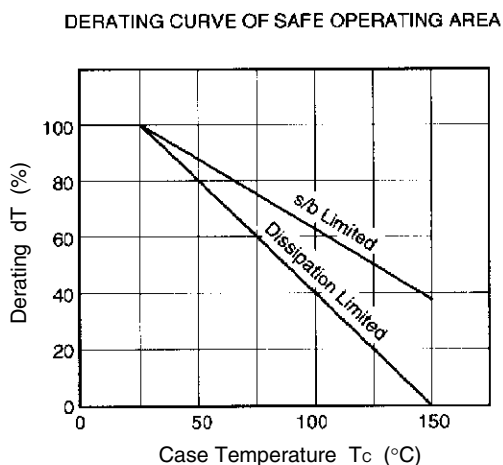
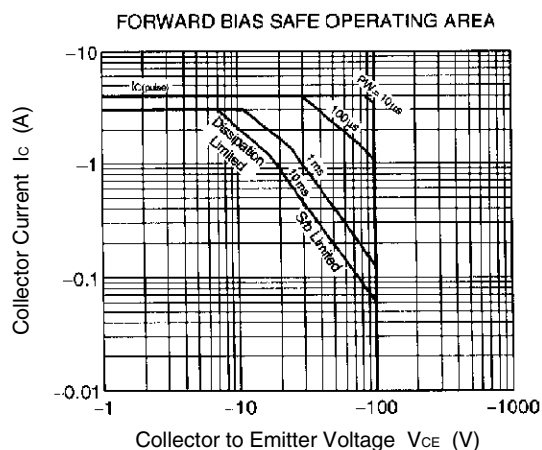
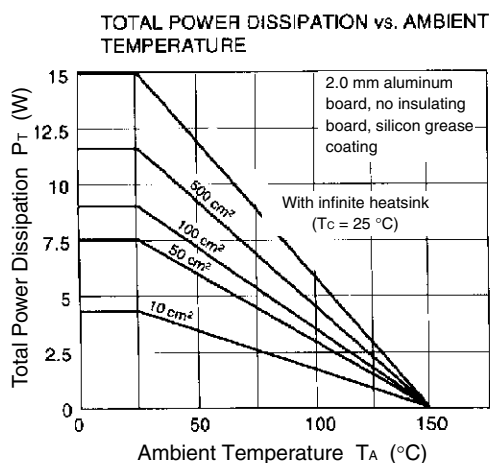
## h<sub>FE</sub> CLASSIFICATION

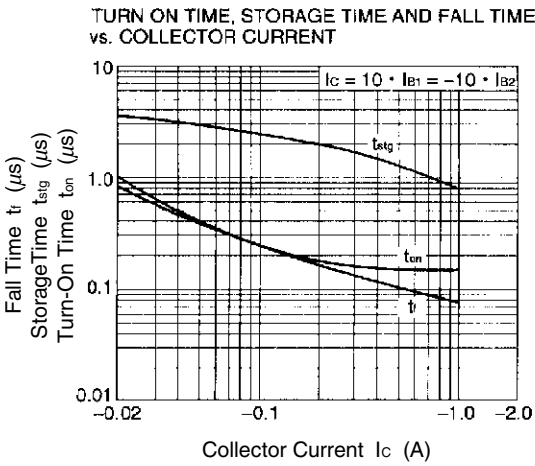
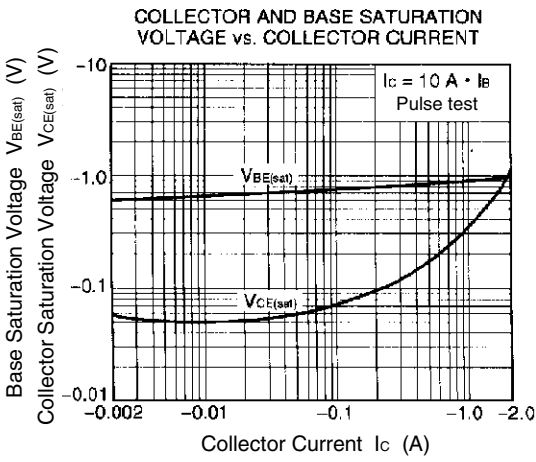
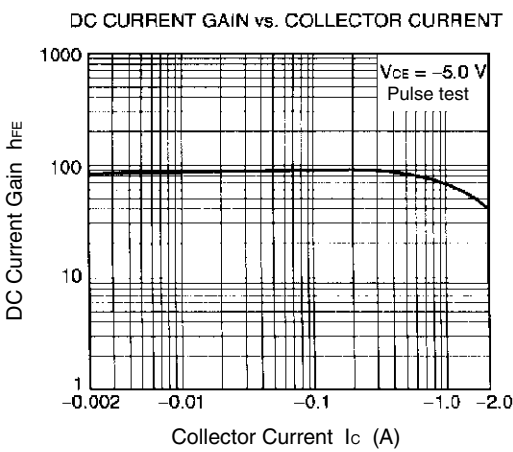
| Marking          | M        | L         | K          |
|------------------|----------|-----------|------------|
| h <sub>FE2</sub> | 40 to 80 | 60 to 120 | 100 to 200 |

## SWITCHING TIME (t<sub>on</sub>, t<sub>stg</sub>, t<sub>f</sub>) TEST CIRCUIT



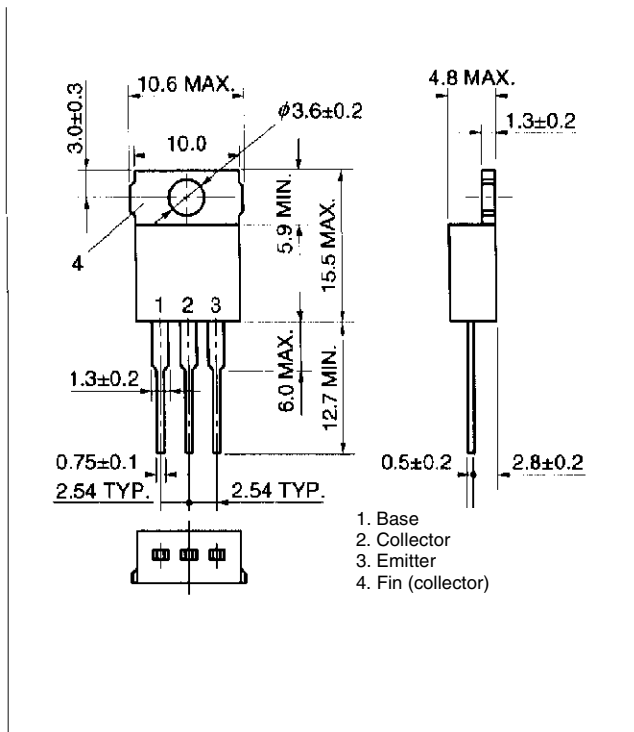
TYPICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ )





PACKAGE DRAWING (UNIT: mm)

TO-220AB (MP-25)



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